Amendments to the Claims

I	1. (Currently Amended) A method of ablation laser-machining, comprising the steps of
2	generating pulses at a repetition rate of 0.1 to 50 MHz-by using one or more
3	semiconductor-chip laser diodes, each a pulse member of the pulses
4	having a pulse-duration of less than three picoseconds;
5	directing a less than 1 square mm-beam of the pulses to toward a work-piece, the
6	beam having a spot area of less than one square millimeter at the surface
7	of the work-piece and with-an ablating pulse-energy-density; and
8	scanning the beam with using a power-driven scanner to ablate a scanned area or
9	the work-piece at least 25 times larger than the beam area spot area of the
10	beam at the surface of the work-piece.
1	2. (Currently Amended) The method of claim 1, wherein the <u>ablating</u> pulse-energy-
2	density is 0.1 to 20 Joules per /square centimeter.
1	3. (Currently Amended) The method of claim 1, wherein the scanned area on the work-
1	5. (Currently Amended) The method of claim 1, wherein the scanned area on the work-
2	piece is at least 100 times larger than the beam area spot area of the beam at the
3	surface of the work-piece.
1	4 (Ouising)) The weether defending 1 wherein the mulge dynation is 50 femalescends to 1
1	4. (Original) The method of claim 1, wherein the pulse-duration is 50 femtoseconds to 1
2	picosecond.
1	5. (Currently Amended) The method of claim 1, wherein the beam area spot area of the
2	beam at the surface of the work-piece is 1 to 2,500 square microns.
_	count at the surface of the work proce

- 1 6. (Currently Amended) The method of claim 1, wherein the ablating pulse-energy-
- density is between 0.1 and 8 Joules/per square centimeter on the work-piece.
- 7. (Currently Amended) The method of claim 1, wherein the pulses are generated at 0.1
- 2 to 50 MHz.
- 8. (Original) The method of claim 1, wherein the beam is scanned in one direction.
- 9. (Original) The method of claim 1, wherein the beam is scanned in two directions.
- 1 10. (Original) The method of claim 1, wherein the beam is scanned in a spiral.
- 1 11. (Currently Amended) A method of ablation laser-machining, comprising the steps of:
- 2 generating 0.6 to 100 MHz pulses at a repetition rate of 0.6 to 100 MHz, a
- duration of a member of the pulses being each pulse having a pulse-
- 4 duration less than three picoseconds;
- directing a less than 1-square mm beam of the pulses toward a work-piece, the
- beam having a spot area at the surface of a work-piece of less than 1
- 7 square millimeter to a work-piece with an ablating pulse-energy density;
- 8 and
- 9 scanning the beam with a power-driven scanner over a scanned area on the work-
- piece at least 25 times larger than the spot area of the beam at the surface
- of the work-piecebeam-area.

- 1 12. (Currently Amended) The method of claim 11, wherein the ablation <u>laser-machining</u>
- 2 is part of a surgical procedure.
- 1. 13. (Currently Amended) The method of claim 11, wherein the ablation <u>laser machining</u>
- is part of a surgical procedure, and the ablating pulse-energy-density is between 1
- and 10 times the an ablation threshold of the work-piece.
- 1 14. (Currently Amended) The method of claim 11, wherein the ablation <u>laser machining</u>
- is part of a surgical procedure, and the ablating pulse-energy-density is between 1
- and 3 times the an ablation threshold of the work-piece.
- 1 15. (Original) The method of claim 11, wherein the pulses are generated by at least one
- 2 optical amplifier.
- 1 16. (Currently Amended) The method of claim 11, wherein the pulses are generated by
- one semiconductor optical amplifier (SOA) and the pulses eontain have an energy
- 3 of less than about 50 micro-Joules per pulse.
- 1 17. (Currently Amended) The method of claim 11, wherein the pulses are generated by
- one fiber amplifier and the pulses contain have an energy of less than 10 micro-
- 3 Joules per pulse.
- 1 18. (Original) The method of claim 11, wherein the beam is rasterized.

1	19.	(New)	A	system	comprising:
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- a semi-conductor chip laser diode configured for generating pulses at a repetition 2 3 rate between 0.1 and 50 MHz; a semiconductor optical amplifier for amplifying the pulses, to generate amplified 4 pulses; 5 a dispersive element configured for compressing the amplified pulses; and 6 a scanning element configured for scanning a beam of the amplified pulses to 7 ablate a scanned area at least 25 times larger than spot area of the beam at 8 9 the surface of the work-piece.
- 1 20. (New) The system of claim 19 further comprising a cauterizing laser.